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Spartan-6 FPGA Data Sheet: DC and Switching Characteristics

DS162 (v3.0) October 17, 2011 **Product Specification**

Spartan-6 FPGA Electrical Characteristics

Spartan®-6 LX and LXT FPGAs are available in various speed grades, with -3 having the highest performance. The DC and AC electrical parameters of the Automotive XA Spartan-6 FPGAs and Defense-grade Spartan-6Q FPGAs devices are equivalent to the commercial specifications except where noted. The timing characteristics of the commercial (XC) -2 speed grade industrial device are the same as for a -2 speed grade commercial device. The -2Q and -3Q speed grades are exclusively for the expanded (Q) temperature range. The timing characteristics are equivalent to those shown for the -2 and -3 speed grades for the Automotive and Defense-grade devices.

Spartan-6 FPGA DC and AC characteristics are specified for commercial (C), industrial (I), and expanded (Q) temperature ranges. Only selected speed grades and/or devices might be available in the industrial or expanded temperature ranges for Automotive and Defense-grade devices. References to device names refer to all available variations of that part number (for example, LX75 could denote XC6SLX75, XA6SLX75, or XQ6SLX75).The Spartan-6 FPGA -3N speed grade designates devices that do not support MCB functionality.

All supply voltage and junction temperature specifications are representative of worst-case conditions. The parameters included are common to popular designs and typical applications.

Available device and package combinations can be found at:

- DS160: *Spartan-6 Family Overview*
- DS170: *Automotive XA Spartan-6 Family Overview*
- DS172: *Defense-Grade Spartan-6Q Family Overview*

This Spartan-6 FPGA data sheet, part of an overall set of documentation on the Spartan-6 family of FPGAs, is available on the Xilinx website at http://www.xilinx.com/support/documentation/spartan-6.htm.

Spartan-6 FPGA DC Characteristics

Table 1: **Absolute Maximum Ratings**(1)

Symbol	Description		Units
V_{CCINT}	Internal supply voltage relative to GND	–0.5 to 1.32	V
V_{CCAUX}	Auxiliary supply voltage relative to GND	–0.5 to 3.75	V
V_{CCO}	Output drivers supply voltage relative to GND	–0.5 to 3.75	V
V_{BATT}	Key memory battery backup supply (LX75, LX75T, LX100, LX100T, LX150, and LX150T only)	–0.5 to 4.05	V
V_{FS}	External voltage supply for eFUSE programming (LX75, LX75T, LX100, LX100T, LX150, and LX150T only)(2)	–0.5 to 3.75	V
V_{REF}	Input reference voltage	–0.5 to 3.75	V

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description					Units
V_{IN} and V_{TS}[3]	I/O input voltage or voltage applied to 3-state output, relative to GND[4]	All user and dedicated I/Os	Commercial	DC	–0.60 to 4.10	V
				20% overshoot duration	–0.75 to 4.25	V
				8% overshoot duration[5]	–0.75 to 4.40	V
			Industrial	DC	–0.60 to 3.95	V
				20% overshoot duration	–0.75 to 4.15	V
				4% overshoot duration[5]	–0.75 to 4.40	V
			Expanded (Q)	DC	–0.60 to 3.95	V
				20% overshoot duration	–0.75 to 4.15	V
				4% overshoot duration[5]	–0.75 to 4.40	V
		Restricted to maximum of 100 user I/Os	Commercial	20% overshoot duration	–0.75 to 4.35	V
				15% overshoot duration[5]	–0.75 to 4.40	V
				10% overshoot duration	–0.75 to 4.45	V
			Industrial	20% overshoot duration	–0.75 to 4.25	V
				10% overshoot duration	–0.75 to 4.35	V
				8% overshoot duration[5]	–0.75 to 4.40	V
			Expanded (Q)	20% overshoot duration	–0.75 to 4.25	V
				10% overshoot duration	–0.75 to 4.35	V
				8% overshoot duration[5]	–0.75 to 4.40	V
T_{STG}	Storage temperature (ambient)				–65 to 150	°C
T_{SOL}	Maximum soldering temperature[6] (TQG144, CPG196, CSG225, CSG324, CSG484, and FTG256)				+260	°C
	Maximum soldering temperature[6] (Pb-free packages: FGG484, FGG676, and FGG900)				+250	°C
	Maximum soldering temperature[6] (Pb packages: CS484, FT256, FG484, FG676, and FG900)				+220	°C
T_j	Maximum junction temperature[6]				+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. When programming eFUSE, $V_{FS} \leq V_{CCAUX}$. Requires up to 40 mA current. For read mode, V_{FS} can be between GND and 3.45 V.
3. I/O absolute maximum limit applied to DC and AC signals. Overshoot duration is the percentage of a data period that the I/O is stressed beyond 3.45V.
4. For I/O operation, refer to UG381: *Spartan-6 FPGA SelectIO Resources User Guide*.
5. Maximum percent overshoot duration to meet 4.40V maximum.
6. For soldering guidelines and thermal considerations, see UG385: *Spartan-6 FPGA Packaging and Pinout Specification*.

Table 2: **Recommended Operating Conditions(1)**

Symbol	Description			Min	Typ	Max	Units
V_{CCINT}	Internal supply voltage relative to GND	-3, -3N, -2	Standard performance(2)	1.14	1.2	1.26	V
		-3, -2	Extended performance(2)	1.2	1.23	1.26	V
		-1L	Standard performance(2)	0.95	1.0	1.05	V
V_{CCAUX}(3)(4)	Auxiliary supply voltage relative to GND	V_{CCAUX} = 2.5V(5)		2.375	2.5	2.625	V
		V_{CCAUX} = 3.3V		3.15	3.3	3.45	V
V_{CCO}(6)(7)(8)	Output supply voltage relative to GND			1.1	–	3.45	V
V_{IN}	Input voltage relative to GND	All I/O standards (except PCI)	Commercial temperature (C)	–0.5	–	4.0	V
			Industrial temperature (I)	–0.5	–	3.95	V
			Expanded (Q) temperature	–0.5	–	3.95	V
		PCI I/O standard(9)		–0.5	–	V_{CCO} + 0.5	V
I_{IN}(10)	Maximum current through pin using PCI I/O standard when forward biasing the clamp diode.(9)		Commercial (C) and Industrial temperature (I)	–	–	10	mA
			Expanded (Q) temperature	–	–	7	mA
V_{BATT}(11)	Battery voltage relative to GND, T_j = 0°C to +85°C (LX75, LX75T, LX100, LX100T, LX150, and LX150T only)			1.0	–	3.6	V
T_j	Junction temperature operating range	Commercial (C) range		0	–	85	°C
		Industrial temperature (I) range		–40	–	100	°C
		Expanded (Q) temperature range		–40	–	125	°C

Notes:

1. All voltages are relative to ground.
2. See *Interface Performances for Memory Interfaces* in Table 25. The extended performance range is specified for designs not using the standard V_{CCINT} voltage range. The standard V_{CCINT} voltage range is used for:
   - Designs that do not use an MCB
   - LX4 devices
   - Devices in the TQG144 or CPG196 packages
   - Devices with the -3N speed grade
3. Recommended maximum voltage droop for V_{CCAUX} is 10 mV/ms.
4. During configuration, if V_{CCO_2} is 1.8V, then V_{CCAUX} must be 2.5V.
5. The -1L devices require V_{CCAUX} = 2.5V when using the LVDS_25, LVDS_33, BLVDS_25, LVPECL_25, RSDS_25, RSDS_33, PPDS_25, and PPDS_33 I/O standards on inputs. LVPECL_33 is not supported in the -1L devices.
6. Configuration data is retained even if V_{CCO} drops to 0V.
7. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
8. For PCI systems, the transmitter and receiver should have common supplies for V_{CCO}.
9. Devices with a -1L speed grade do not support Xilinx PCI IP.
10. Do not exceed a total of 100 mA per bank.
11. V_{BATT} is required to maintain the battery backed RAM (BBR) AES key when V_{CCAUX} is not applied. Once V_{CCAUX} is applied, V_{BATT} can be unconnected. When BBR is not used, Xilinx recommends connecting to V_{CCAUX} or GND. However, V_{BATT} can be unconnected.

Table 3: **eFUSE Programming Conditions(1)**

Symbol	Description	Min	Typ	Max	Units
V_{FS}(2)	External voltage supply	3.2	3.3	3.4	V
I_{FS}	V_{FS} supply current	–	–	40	mA
V_{CCAUX}	Auxiliary supply voltage relative to GND	3.2	3.3	3.45	V
R_{FUSE}(3)	External resistor from R_{FUSE} pin to GND	1129	1140	1151	Ω
V_{CCINT}	Internal supply voltage relative to GND	1.14	1.2	1.26	V
t_j	Temperature range	15	–	85	°C

Notes:

1. These specifications apply during programming of the eFUSE AES key. Programming is only supported through JTAG.The AES key is only supported in the following devices: LX75, LX75T, LX100, LX100T, LX150, and LX150T.
2. When programming eFUSE, V_{FS} must be less than or equal to V_{CCAUX}. When not programming or when eFUSE is not used, Xilinx recommends connecting V_{FS} to GND. However, V_{FS} can be between GND and 3.45 V.
3. An R_{FUSE} resistor is required when programming the eFUSE AES key. When not programming or when eFUSE is not used, Xilinx recommends connecting the R_{FUSE} pin to V_{CCAUX} or GND. However, R_{FUSE} can be unconnected.

Table 4: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description		Min	Typ	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)		0.8	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)		2.0	–	–	V
I_{REF}	V_{REF} leakage current per pin for commercial (C) and industrial (I) devices		–10	–	10	µA
	V_{REF} leakage current per pin for expanded (Q) devices		–15	–	15	µA
I_L	Input or output leakage current per pin (sample-tested) for commercial (C) and industrial (I) devices		–10	–	10	µA
	Input or output leakage current per pin (sample-tested) for expanded (Q) devices		–15	–	15	µA
I_{HS}	Leakage current on pins during hot socketing with FPGA unpowered	All pins except PROGRAM_B, DONE, and JTAG pins when HSWAPEN = 1	–20	–	20	µA
		PROGRAM_B, DONE, and JTAG pins, or other pins when HSWAPEN = 0	$I_{HS} + I_{RPU}$			µA
C_{IN}[1]	Die input capacitance at the pad		–	–	10	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V or V_{CCAUX} = 3.3V		200	–	500	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V or V_{CCAUX} = 2.5V		120	–	350	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V		60	–	200	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V		40	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V		12	–	100	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = V_{CCO}, V_{CCAUX} = 3.3V		200	–	550	µA
	Pad pull-down (when selected) @ V_{IN} = V_{CCO}, V_{CCAUX} = 2.5V		140	–	400	µA
I_{BATT}[2]	Battery supply current		–	–	150	nA
R_{DT}[3]	Resistance of optional input differential termination circuit, V_{CCAUX} = 3.3V		–	100	–	Ω
R_{IN_TERM}[5]	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_25) for commercial (C) and industrial (I) devices		23	25	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_25) for expanded (Q) devices		20	25	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_50) for commercial (C) and industrial (I) devices		39	50	72	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_50) for expanded (Q) devices		32	50	74	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_75) for commercial (C) and industrial (I) devices		56	75	109	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO} (UNTUNED_SPLIT_75) for expanded (Q) devices		47	75	115	Ω
R_{OUT_TERM}	Thevenin equivalent resistance of programmable output termination (UNTUNED_25)		11	25	52	Ω
	Thevenin equivalent resistance of programmable output termination (UNTUNED_50)		21	50	96	Ω
	Thevenin equivalent resistance of programmable output termination (UNTUNED_75)		29	75	145	Ω

Notes:

1. The C_{IN} measurement represents the die capacitance at the pad, not including the package.
2. Maximum value specified for worst case process at 25°C. LX75, LX75T, LX100, LX100T, LX150, and LX150T only.
3. Refer to IBIS models for R_{DT} variation and for values at V_{CCAUX} = 2.5V. IBIS values for R_{DT} are valid for all temperature ranges.
4. V_{CCO2} is not required for data retention. The minimum V_{CCO2} for power-on reset and configuration is 1.65V.
5. Termination resistance to a V_{CCO}/2 level.

Quiescent Current

Typical values for quiescent supply current are specified at nominal voltage, 25°C junction temperatures (T_j). Quiescent supply current is specified by speed grade for Spartan-6 devices. Xilinx recommends analyzing static power consumption using the XPOWER™ Estimator (XPE) tool (download at http://www.xilinx.com/power) for conditions other than those specified in Table 5.

Table 5: **Typical Quiescent Supply Current**

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
I_{CCINTQ}	Quiescent V_{CCINT} supply current	LX4	4.0	4.0	4.0	2.4	mA
		LX9	4.0	4.0	4.0	2.4	mA
		LX16	6.0	6.0	6.0	4.0	mA
		LX25	11.0	11.0	11.0	6.6	mA
		LX25T	11.0	11.0	11.0	N/A	mA
		LX45	15.0	15.0	15.0	9.0	mA
		LX45T	15.0	15.0	15.0	N/A	mA
		LX75	29.0	29.0	29.0	17.4	mA
		LX75T	29.0	29.0	29.0	N/A	mA
		LX100	36.0	36.0	36.0	21.6	mA
		LX100T	36.0	36.0	36.0	N/A	mA
		LX150	51.0	51.0	51.0	31.0	mA
		LX150T	51.0	51.0	51.0	N/A	mA
I_{CCOQ}	Quiescent V_{CCO} supply current	LX4	1.0	1.0	1.0	1.0	mA
		LX9	1.0	1.0	1.0	1.0	mA
		LX16	2.0	2.0	2.0	2.0	mA
		LX25	2.0	2.0	2.0	2.0	mA
		LX25T	2.0	2.0	2.0	N/A	mA
		LX45	3.0	3.0	3.0	3.0	mA
		LX45T	3.0	3.0	3.0	N/A	mA
		LX75	4.0	4.0	4.0	4.0	mA
		LX75T	4.0	4.0	4.0	N/A	mA
		LX100	5.0	5.0	5.0	5.0	mA
		LX100T	5.0	5.0	5.0	N/A	mA
		LX150	7.0	7.0	7.0	7.0	mA
		LX150T	7.0	7.0	7.0	N/A	mA

Table 5: **Typical Quiescent Supply Current *(Cont'd)***

Symbol	Description	Device	Speed Grade				Units
			-3	-3N	-2	-1L	
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current	LX4	2.5	2.5	2.5	2.5	mA
		LX9	2.5	2.5	2.5	2.5	mA
		LX16	3.0	3.0	3.0	3.0	mA
		LX25	4.0	4.0	4.0	4.0	mA
		LX25T	4.0	4.0	4.0	N/A	mA
		LX45	5.0	5.0	5.0	5.0	mA
		LX45T	5.0	5.0	5.0	N/A	mA
		LX75	7.0	7.0	7.0	7.0	mA
		LX75T	7.0	7.0	7.0	N/A	mA
		LX100	9.0	9.0	9.0	9.0	mA
		LX100T	9.0	9.0	9.0	N/A	mA
		LX150	12.0	12.0	12.0	12.0	mA
		LX150T	12.0	12.0	12.0	N/A	mA

Notes:

1. Typical values are specified at nominal voltage, 25°C junction temperatures (Tj). Industrial (I) grade devices have the same typical values as commercial (C) grade devices at 25°C, but higher values at 100°C. Use the XPE tool to calculate 100°C values. Nominal V_{CCINT} is 1.20V; use the XPE tool to calculate 1.23V values for the nominal V_{CCINT} of the extended performance range.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. If differential signaling is used, more accurate quiescent current estimates can be obtained by using the XPOWER Estimator (XPE) or XPOWER Analyzer (XPA) tools.

Table 6: **Power Supply Ramp Time**

Symbol	Description	Speed Grade	Ramp Time	Units
V_{CCINTR}	Internal supply voltage ramp time	-3, -3N, -2	0.20 to 50.0	ms
		-1L	0.20 to 40.0	ms
V_{CCO2}(1)	Output drivers bank 2 supply voltage ramp time	All	0.20 to 50.0	ms
V_{CCAUXR}	Auxiliary supply voltage ramp time	All	0.20 to 50.0	ms

Notes:

1. The minimum V_{CCO2} for power-on reset and configuration is 1.65V.
2. Spartan-6 FPGAs require a certain amount of supply current during power-on to insure proper device initialization. The actual current consumed depends on the power-on ramp rate of the power supply. Use the XPOWER Estimator (XPE) or XPOWER Analyzer (XPA) tools to estimate current drain on these supplies. Spartan-6 devices do not have a required power-on sequence.

SelectIO™ Interface DC Input and Output Levels

Table 7: **Recommended Operating Conditions for User I/Os Using Single-Ended Standards**

I/O Standard	V_{CCO} for Drivers[1]			V_{REF} for Inputs		
	V, Min	V, Nom	V, Max	V, Min	V, Nom	V, Max
LVTTL	3.0	3.3	3.45	V_{REF} is not used for these I/O standards		
LVCMOS33	3.0	3.3	3.45			
LVCMOS25	2.3	2.5	2.7			
LVCMOS18	1.65	1.8	1.95			
LVCMOS18_JEDEC	1.65	1.8	1.95			
LVCMOS15	1.4	1.5	1.6			
LVCMOS15_JEDEC	1.4	1.5	1.6			
LVCMOS12	1.1	1.2	1.3			
LVCMOS12_JEDEC	1.1	1.2	1.3			
PCI33_3[2]	3.0	3.3	3.45			
PCI66_3[2]	3.0	3.3	3.45			
I2C	2.7	3.0	3.45			
SMBUS	2.7	3.0	3.45			
SDIO	3.0	3.3	3.45			
MOBILE_DDR	1.7	1.8	1.9			
HSTL_I	1.4	1.5	1.6	0.68	0.75	0.9
HSTL_II	1.4	1.5	1.6	0.68	0.75	0.9
HSTL_III	1.4	1.5	1.6	–	0.9	–
HSTL_I_18	1.7	1.8	1.9	0.8	0.9	1.1
HSTL_II_18	1.7	1.8	1.9	–	0.9	–
HSTL_III_18	1.7	1.8	1.9	–	1.1	–
SSTL3_I	3.0	3.3	3.45	1.3	1.5	1.7
SSTL3_II	3.0	3.3	3.45	1.3	1.5	1.7
SSTL2_I	2.3	2.5	2.7	1.13	1.25	1.38
SSTL2_II	2.3	2.5	2.7	1.13	1.25	1.38
SSTL18_I	1.7	1.8	1.9	0.833	0.9	0.969
SSTL18_II	1.7	1.8	1.9	0.833	0.9	0.969
SSTL15_II	1.425	1.5	1.575	0.69	0.75	0.81

Notes:

1. V_{CCO} range required when using I/O standard for an output. Also required for MOBILE_DDR, PCI33_3, LVCMOS18_JEDEC, LVCMOS15_JEDEC, and LVCMOS12_JEDEC inputs, and for LVCMOS25 inputs when V_{CCAUX} = 3.3V.
2. For PCI systems, the transmitter and receiver should have common supplies for V_{CCO}.

Table 8: **Recommended Operating Conditions for User I/Os Using Differential Signal Standards**

I/O Standard	V_{CCO} for Drivers		
	V, Min	V, Nom	V, Max
LVDS_33	3.0	3.3	3.45
LVDS_25	2.25	2.5	2.75
BLVDS_25	2.25	2.5	2.75
MINI_LVDS_33	3.0	3.3	3.45
MINI_LVDS_25	2.25	2.5	2.75
LVPECL_33(1)	N/A–Inputs Only		
LVPECL_25	N/A–Inputs Only		
RSDS_33	3.0	3.3	3.45
RSDS_25	2.25	2.5	2.75
TMDS_33(1)	3.14	3.3	3.45
PPDS_33	3.0	3.3	3.45
PPDS_25	2.25	2.5	2.75
DISPLAY_PORT	2.3	2.5	2.7
DIFF_MOBILE_DDR	1.7	1.8	1.9
DIFF_HSTL_I	1.4	1.5	1.6
DIFF_HSTL_II	1.4	1.5	1.6
DIFF_HSTL_III	1.4	1.5	1.6
DIFF_HSTL_I_18	1.7	1.8	1.9
DIFF_HSTL_II_18	1.7	1.8	1.9
DIFF_HSTL_III_18	1.7	1.8	1.9
DIFF_SSTL3_I	3.0	3.3	3.45
DIFF_SSTL3_II	3.0	3.3	3.45
DIFF_SSTL2_I	2.3	2.5	2.7
DIFF_SSTL2_II	2.3	2.5	2.7
DIFF_SSTL18_I	1.7	1.8	1.9
DIFF_SSTL18_II	1.7	1.8	1.9
DIFF_SSTL15_II	1.425	1.5	1.575

Notes:

1. LVPECL_33 and TMDS_33 inputs require V_{CCAUX} = 3.3V nominal.

In Table 9 and Table 10, values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 9: **Single-Ended I/O Standard DC Input and Output Levels**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
LVTTL	–0.5	0.8	2.0	4.1	0.4	2.4	Note 2	Note 2
LVCMOS33	–0.5	0.8	2.0	4.1	0.4	V_{CCO} – 0.4	Note 2	Note 2
LVCMOS25	–0.5	0.7	1.7	4.1	0.4	V_{CCO} – 0.4	Note 2	Note 2
LVCMOS18	–0.5	0.38	0.8	4.1	0.45	V_{CCO} – 0.45	Note 2	Note 2
LVCMOS18 (-1L)	–0.5	0.33	0.71	4.1	0.45	V_{CCO} – 0.45	Note 2	Note 2
LVCMOS18_JEDEC	–0.5	35% V_{CCO}	65% V_{CCO}	4.1	0.45	V_{CCO} – 0.45	Note 2	Note 2
LVCMOS15	–0.5	0.38	0.8	4.1	25% V_{CCO}	75% V_{CCO}	Note 3	Note 3
LVCMOS15 (-1L)	–0.5	0.33	0.71	4.1	25% V_{CCO}	75% V_{CCO}	Note 3	Note 3
LVCMOS15_JEDEC	–0.5	35% V_{CCO}	65% V_{CCO}	4.1	25% V_{CCO}	75% V_{CCO}	Note 3	Note 3
LVCMOS12	–0.5	0.38	0.8	4.1	0.4	V_{CCO} – 0.4	Note 4	Note 4
LVCMOS12 (-1L)	–0.5	0.33	0.71	4.1	0.4	V_{CCO} – 0.4	Note 4	Note 4
LVCMOS12_JEDEC	–0.5	35% V_{CCO}	65% V_{CCO}	4.1	0.4	V_{CCO} – 0.4	Note 4	Note 4
PCI33_3	–0.5	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.5	10% V_{CCO}	90% V_{CCO}	1.5	–0.5
PCI66_3	–0.5	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.5	10% V_{CCO}	90% V_{CCO}	1.5	–0.5
I2C	–0.5	25% V_{CCO}	70% V_{CCO}	4.1	20% V_{CCO}	–	3	–
SMBUS	–0.5	0.8	2.1	4.1	0.4	–	4	–
SDIO	–0.5	12.5% V_{CCO}	75% V_{CCO}	4.1	12.5% V_{CCO}	75% V_{CCO}	0.1	–0.1
MOBILE_DDR	–0.5	20% V_{CCO}	80% V_{CCO}	4.1	10% V_{CCO}	90% V_{CCO}	0.1	–0.1
HSTL_I	–0.5	V_{REF} – 0.1	V_{REF} + 0.1	4.1	0.4	V_{CCO} – 0.4	8	–8
HSTL_II	–0.5	V_{REF} – 0.1	V_{REF} + 0.1	4.1	0.4	V_{CCO} – 0.4	16	–16
HSTL_III	–0.5	V_{REF} – 0.1	V_{REF} + 0.1	4.1	0.4	V_{CCO} – 0.4	24	–8
HSTL_I_18	–0.5	V_{REF} – 0.1	V_{REF} + 0.1	4.1	0.4	V_{CCO} – 0.4	11	–11
HSTL_II_18	–0.5	V_{REF} – 0.1	V_{REF} + 0.1	4.1	0.4	V_{CCO} – 0.4	22	–22
HSTL_III_18	–0.5	V_{REF} – 0.1	V_{REF} + 0.1	4.1	0.4	V_{CCO} – 0.4	30	–11
SSTL3_I	–0.5	V_{REF} – 0.2	V_{REF} + 0.2	4.1	V_{TT} – 0.6	V_{TT} + 0.6	8	–8
SSTL3_II	–0.5	V_{REF} – 0.2	V_{REF} + 0.2	4.1	V_{TT} – 0.8	V_{TT} + 0.8	16	–16
SSTL2_I	–0.5	V_{REF} – 0.15	V_{REF} + 0.15	4.1	V_{TT} – 0.61	V_{TT} + 0.61	8.1	–8.1
SSTL2_II	–0.5	V_{REF} – 0.15	V_{REF} + 0.15	4.1	V_{TT} – 0.81	V_{TT} + 0.81	16.2	–16.2
SSTL18_I	–0.5	V_{REF} – 0.125	V_{REF} + 0.125	4.1	V_{TT} – 0.47	V_{TT} + 0.47	6.7	–6.7
SSTL18_II	–0.5	V_{REF} – 0.125	V_{REF} + 0.125	4.1	V_{TT} – 0.60	V_{TT} + 0.60	13.4	–13.4
SSTL15_II	–0.5	V_{REF} – 0.1	V_{REF} + 0.1	4.1	V_{TT} – 0.4	V_{TT} + 0.4	13.4	–13.4

Notes:

1. Tested according to relevant specifications.
2. Using drive strengths of 2, 4, 6, 8, 12, 16, or 24 mA.
3. Using drive strengths of 2, 4, 6, 8, 12, or 16 mA.
4. Using drive strengths of 2, 4, 6, 8, or 12 mA.
5. For more information, refer to UG381: *Spartan-6 FPGA SelectIO Resources User Guide*.

Table 10: **Differential I/O Standard DC Input and Output Levels**

I/O Standard	V_{ID}		V_{ICM}		V_{OD}		V_{OCM}		V_{OH}	V_{OL}
	mV, Min	mV, Max	V, Min	V, Max	mV, Min	mV, Max	V, Min	V, Max	V, Min	V, Max
LVDS_33[2][3]	100	600	0.3	2.35	247	454	1.125	1.375	–	–
LVDS_25[2][3]	100	600	0.3	2.35	247	454	1.125	1.375	–	–
BLVDS_25[2][3]	100	–	0.3	2.35	240	460	Typical 50% V_{CCO}		–	–
MINI_LVDS_33	200	600	0.3	1.95	300	600	1.0	1.4	–	–
MINI_LVDS_25	200	600	0.3	1.95	300	600	1.0	1.4	–	–
LVPECL_33[2][3]	100	1000	0.3	2.8[1]	Inputs only					
LVPECL_25[2][3]	100	1000	0.3	1.95	Inputs only					
RSDS_33[2][3]	100	–	0.3	1.5	100	400	1.0	1.4	–	–
RSDS_25[2][3]	100	–	0.3	1.5	100	400	1.0	1.4	–	–
TMDS_33	150	1200	2.7	3.23[1]	400	800	V_{CCO} – 0.405	V_{CCO} – 0.190	–	–
PPDS_33[2][3]	100	400	0.2	2.3	100	400	0.5	1.4	–	–
PPDS_25[2][3]	100	400	0.2	2.3	100	400	0.5	1.4	–	–
DISPLAY_PORT	190	1260	0.3	2.35	–	–	Typical 50% V_{CCO}		–	–
DIFF_MOBILE_DDR	100	–	0.78	1.02	–	–	–	–	90% V_{CCO}	10% V_{CCO}
DIFF_HSTL_I	100	–	0.68	0.9	–	–	–	–	V_{CCO} – 0.4	0.4
DIFF_HSTL_II	100	–	0.68	0.9	–	–	–	–	V_{CCO} – 0.4	0.4
DIFF_HSTL_III	100	–	0.68	0.9	–	–	–	–	V_{CCO} – 0.4	0.4
DIFF_HSTL_I_18	100	–	0.8	1.1	–	–	–	–	V_{CCO} – 0.4	0.4
DIFF_HSTL_II_18	100	–	0.8	1.1	–	–	–	–	V_{CCO} – 0.4	0.4
DIFF_HSTL_III_18	100	–	0.8	1.1	–	–	–	–	V_{CCO} – 0.4	0.4
DIFF_SSTL3_I	100	–	1.0	1.9	–	–	–	–	V_{TT} + 0.6	V_{TT} – 0.6
DIFF_SSTL3_II	100	–	1.0	1.9	–	–	–	–	V_{TT} + 0.8	V_{TT} – 0.8
DIFF_SSTL2_I	100	–	1.0	1.5	–	–	–	–	V_{TT} + 0.61	V_{TT} – 0.61
DIFF_SSTL2_II	100	–	1.0	1.5	–	–	–	–	V_{TT} + 0.81	V_{TT} – 0.81
DIFF_SSTL18_I	100	–	0.7	1.1	–	–	–	–	V_{TT} + 0.47	V_{TT} – 0.47
DIFF_SSTL18_II	100	–	0.7	1.1	–	–	–	–	V_{TT} + 0.6	V_{TT} – 0.6
DIFF_SSTL15_II	100	–	0.55	0.95	–	–	–	–	V_{TT} + 0.4	V_{TT} – 0.4

Notes:

1. LVPECL_33 and TMDS_33 maximum V_{ICM} is the lower of V (maximum) or V_{CCAUX} – (V_{ID}/2)
2. When V_{CCAUX} = 3.3V, the DCD can be higher than 5% for V_{ICM} < 0.7V when using these I/O standards: LVDS_25, LVDS_33, BLVDS_25, LVPECL_25, LVPECL_33, RSDS_25, RSDS_33, PPDS_25, and PPDS_33.
3. The -1L devices require V_{CCAUX} = 2.5V when using the LVDS_25, LVDS_33, BLVDS_25, LVPECL_25, RSDS_25, RSDS_33, PPDS_25, and PPDS_33 I/O standards on inputs. LVPECL_33 is not supported in the -1L devices.

eFUSE Read Endurance

Table 11 lists the minimum guaranteed number of read cycle operations for Device DNA and for the AES eFUSE key. For more information, see UG380: *Spartan-6 FPGA Configuration User Guide*.

Table 11: **eFUSE Read Endurance**

Symbol	Description	Speed Grade				Units (Min)
		-3	-3N	-2	-1L	
DNA_CYCLES	Number of DNA_PORT READ operations or JTAG ISC_DNA read command operations. Unaffected by SHIFT operations.	30,000,000				Read Cycles
AES_CYCLES	Number of JTAG FUSE_KEY or FUSE_CNTL read command operations. Unaffected by SHIFT operations.	30,000,000				Read Cycles

GTP Transceiver Specifications

GTP transceivers are available in the Spartan-6 LXT devices. See DS160: *Spartan-6 Family Overview* for more information.

GTP Transceiver DC Characteristics

Table 12: **Absolute Maximum Ratings for GTP Transceivers(1)**

Symbol	Description	Mln	Max	Units
MGTAVCC	Analog supply voltage for the GTP transmitter and receiver circuits relative to GND	–0.5	1.32	V
MGTAVTTTX	Analog supply voltage for the GTP transmitter termination circuit relative to GND	–0.5	1.32	V
MGTAVTTRX	Analog supply voltage for the GTP receiver termination circuit relative to GND	–0.5	1.32	V
MGTAVCCPLL	Analog supply voltage for the GTP transmitter and receiver PLL circuits relative to GND	–0.5	1.32	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTP transceiver bank (top or bottom)	–0.5	1.32	V
V_{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	–0.5	1.32	V
$V_{MGTREFCLK}$	Reference clock absolute input voltage	–0.5	1.32	V

Notes:
1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.

Table 13: **Recommended Operating Conditions for GTP Transceivers(1)(2)(3)**

Symbol	Description	Min	Typ	Max	Units
MGTAVCC	Analog supply voltage for the GTP transmitter and receiver circuits relative to GND	1.14	1.20	1.26	V
MGTAVTTTX	Analog supply voltage for the GTP transmitter termination circuit relative to GND	1.14	1.20	1.26	V
MGTAVTTRX	Analog supply voltage for the GTP receiver termination circuit relative to GND	1.14	1.20	1.26	V
MGTAVCCPLL	Analog supply voltage for the GTP transmitter and receiver PLL circuits relative to GND	1.14	1.20	1.26	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTP transceiver bank (top or bottom)	1.14	1.20	1.26	V

Notes:
1. Each voltage listed requires the filter circuit described in UG386: *Spartan-6 FPGA GTP Transceivers User Guide*.
2. Voltages are specified for the temperature range of T_j = –40°C to +125°C.
3. The voltage level of MGTAVCCPLL must not exceed the voltage level of MGTAVCC +10mV. The voltage level of MGTAVCC must not exceed the voltage level of MGTAVCCPLL.

Table 14: **GTP Transceiver Current Supply (per Lane)**

Symbol	Description	Typ[1]	Max	Units
$I_{MGTAVCC}$	GTP transceiver internal analog supply current	40.4	Note 2	mA
$I_{MGTAVTTTX}$	GTP transmitter termination supply current	27.4		mA
$I_{MGTAVTTRX}$	GTP receiver termination supply current	13.6		mA
$I_{MGTAVCCPLL}$	GTP transmitter and receiver PLL supply current	28.7		mA
$R_{MGTRREF}$	Precision reference resistor for internal calibration termination	50.0 ± 1% tolerance		Ω

Notes:
1. Typical values are specified at nominal voltage, 25°C, with a 2.5 Gb/s line rate, with a shared PLL use mode.
2. Values for currents of other transceiver configurations and conditions can be obtained by using the XPOWER Estimator (XPE) or XPOWER Analyzer (XPA) tools.

Table 15: **GTP Transceiver Quiescent Supply Current (per Lane)[1][2][3][4]**

Symbol	Description	Typ[5]	Max	Units
$I_{MGTAVCCQ}$	Quiescent MGTAVCC supply current	1.7	Note 2	mA
$I_{MGTAVTTTXQ}$	Quiescent MGTAVTTTX supply current	0.1		mA
$I_{MGTAVTTRXQ}$	Quiescent MGTAVTTRX supply current	1.2		mA
$I_{MGTAVCCPLLQ}$	Quiescent MGTAVCCPLL supply current	1.0		mA

Notes:
1. Device powered and unconfigured.
2. Currents for conditions other than values specified in this table can be obtained by using the XPOWER Estimator (XPE) or XPOWER Analyzer (XPA) tools.
3. GTP transceiver quiescent supply current for an entire device can be calculated by multiplying the values in this table by the number of available GTP transceivers.
4. Does not include power-up MGTAVTTRCAL supply current during device configuration.
5. Typical values are specified at nominal voltage, 25°C.

GTP Transceiver DC Input and Output Levels

Table 16 summarizes the DC output specifications of the GTP transceivers in Spartan-6 FPGAs. Figure 1 shows the single-ended output voltage swing. Figure 2 shows the peak-to-peak differential output voltage.

Consult UG386: *Spartan-6 FPGA GTP Transceivers User Guide* for further details.

Table 16: **GTP Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPIN}	Differential peak-to-peak input voltage	External AC coupled	140	–	2000	mV
V_{IN}	Absolute input voltage	DC coupled MGTAVTTRX = 1.2V	–400	–	MGTAVTTRX	mV
V_{CMIN}	Common mode input voltage	DC coupled MGTAVTTRX = 1.2V	–	3/4 MGTAVTTRX	–	mV
DV_{PPOUT}	Differential peak-to-peak output voltage(1)	Transmitter output swing is set to maximum setting	–	–	1000	mV
V_{SEOUT}	Single-ended output voltage swing(1)		–	–	500	mV
$V_{CMOUTDC}$	Common mode output voltage	Equation based	MGTAVTTTX – V_{SEOUT}/2			mV
R_{IN}	Differential input resistance		80	100	130	Ω
R_{OUT}	Differential output resistance		80	100	130	Ω
T_{OSKEW}	Transmitter output skew		–	–	15	ps
C_{EXT}	Recommended external AC coupling capacitor(2)		75	100	200	nF

Notes:
1. The output swing and preemphasis levels are programmable using the attributes discussed in UG386: *Spartan-6 FPGA GTP Transceivers User Guide* and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

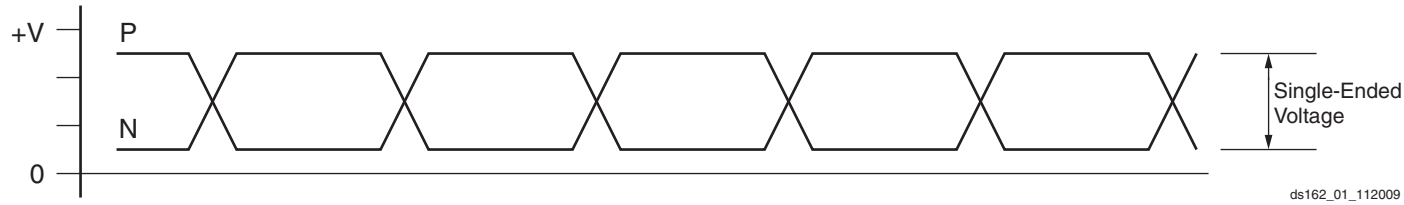

Figure 1: **Single-Ended Peak-to-Peak Voltage**

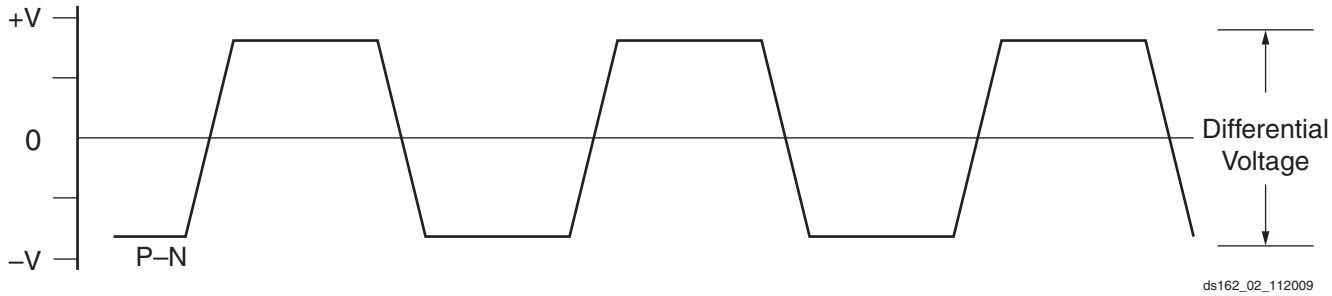

Figure 2: **Differential Peak-to-Peak Voltage**

Table 17 summarizes the DC specifications of the clock input of the GTP transceiver. Consult UG386: *Spartan-6 FPGA GTP Transceivers User Guide* for further details.

Table 17: **GTP Transceiver Clock DC Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage	200	800	2000	mV
R_{IN}	Differential input resistance	80	100	120	Ω
C_{EXT}	Required external AC coupling capacitor	–	100	–	nF

GTP Transceiver Switching Characteristics

Consult UG386: *Spartan-6 FPGA GTP Transceivers User Guide* for further information.

Table 18: **GTP Transceiver Performance**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
F_{GTPMAX}	Maximum GTP transceiver data rate	3.2	3.2	2.7	N/A	Gb/s
$F_{GTPRANGE1}$	GTP transceiver data rate range when PLL_TXDIVSEL_OUT = 1	1.88 to 3.2	1.88 to 3.2	1.88 to 2.7	N/A	Gb/s
$F_{GTPRANGE2}$	GTP transceiver data rate range when PLL_TXDIVSEL_OUT = 2	0.94 to 1.62	0.94 to 1.62	0.94 to 1.62	N/A	Gb/s
$F_{GTPRANGE3}$	GTP transceiver data rate range when PLL_TXDIVSEL_OUT = 4	0.6 to 0.81	0.6 to 0.81	0.6 to 0.81	N/A	Gb/s
$F_{GPLLMAX}$	Maximum PLL frequency	1.62	1.62	1.62	N/A	GHz
$F_{GPLLMIN}$	Minimum PLL frequency	0.94	0.94	0.94	N/A	GHz

Table 19: **GTP Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
$F_{GTPDRPCLK}$	GTP transceiver DCLK (DRP clock) maximum frequency	125	125	100	N/A	MHz

Table 20: **GTP Transceiver Reference Clock Switching Characteristics**

Symbol	Description	Conditions	All LXT Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range		60	–	160	MHz
T_{RCLK}	Reference clock rise time	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle	Transceiver PLL only	45	50	55	%
T_{LOCK}	Clock recovery frequency acquisition time	Initial PLL lock	–	–	1	ms
T_{PHASE}	Clock recovery phase acquisition time	Lock to data after PLL has locked to the reference clock	–	–	200	µs

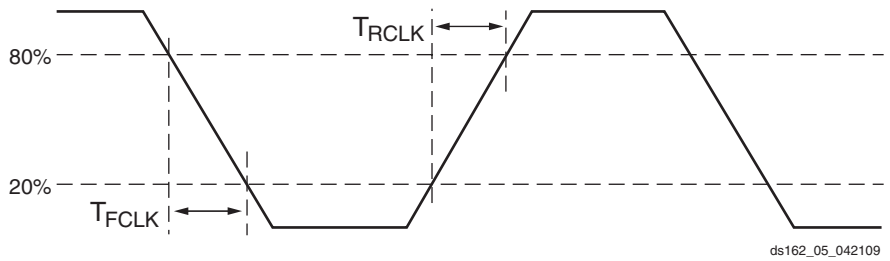

Figure 3: **Reference Clock Timing Parameters**

Table 21: **GTP Transceiver User Clock Switching Characteristics(1)**

Symbol	Description	Conditions	Speed Grade				Units
			-3	-3N	-2	-1L	
F_{TXOUT}	TXOUTCLK maximum frequency		320	320	270	N/A	MHz
F_{RXREC}	RXRECCLK maximum frequency		320	320	270	N/A	MHz
T_{RX}	RXUSRCLK maximum frequency		320	320	270	N/A	MHz
T_{RX2}	RXUSRCLK2 maximum frequency	1 byte interface	156.25	156.25	125	N/A	MHz
		2 byte interface	160	160	125	N/A	MHz
		4 byte interface	80	80	67.5	N/A	MHz
T_{TX}	TXUSRCLK maximum frequency		320	320	270	N/A	MHz
T_{TX2}	TXUSRCLK2 maximum frequency	1 byte interface	156.25	156.25	125	N/A	MHz
		2 byte interface	160	160	125	N/A	MHz
		4 byte interface	80	80	67.5	N/A	MHz

Notes:
1. Clocking must be implemented as described in UG386: *Spartan-6 FPGA GTP Transceivers User Guide*.

Table 22: **GTP Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
T_{RTX}	TX Rise time	20%–80%	–	140	–	ps
T_{FTX}	TX Fall time	80%–20%	–	120	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	400	ps
$V_{TXOOBVDPP}$	Electrical idle amplitude		–	–	20	mV
$T_{TXOOBTRANSITION}$	Electrical idle transition time		–	–	50	ns
$T_{J3.125}$	Total Jitter(2)	3.125 Gb/s	–	–	0.35	UI
$D_{J3.125}$	Deterministic Jitter(2)		–	–	0.15	UI
$T_{J2.5}$	Total Jitter(2)	2.5 Gb/s	–	–	0.33	UI
$D_{J2.5}$	Deterministic Jitter(2)		–	–	0.15	UI
$T_{J1.62}$	Total Jitter(2)	1.62 Gb/s	–	–	0.20	UI
$D_{J1.62}$	Deterministic Jitter(2)		–	–	0.10	UI
$T_{J1.25}$	Total Jitter(2)	1.25 Gb/s	–	–	0.20	UI
$D_{J1.25}$	Deterministic Jitter(2)		–	–	0.10	UI
T_{J614}	Total Jitter(2)	614 Mb/s	–	–	0.10	UI
D_{J614}	Deterministic Jitter(2)		–	–	0.05	UI

Notes:
1. Using same REFCLK input with TXENPMAPHASEALIGN enabled for up to four consecutive GTP transceiver sites.
2. Using PLL_DIVSEL_FB = 2, INTDATAWIDTH = 1. These values are NOT intended for protocol specific compliance determinations.

Table 23: **GTP Transceiver Receiver Switching Characteristics**

Symbol	Description			Min	Typ	Max	Units
$T_{RXELECIDLE}$	Time for RXELECIDLE to respond to loss or restoration of data			–	75	–	ns
$R_{XOOBVDPP}$	OOB detect threshold peak-to-peak			60	–	150	mV
R_{XSST}	Receiver spread-spectrum tracking(1)		Modulated @ 33 KHz	–5000	–	0	ppm
R_{XRL}	Run length (CID)	Internal AC capacitor bypassed		–	–	150	UI
$R_{XPPMTOL}$	Data/REFCLK PPM offset tolerance	CDR 2nd-order loop disabled		–200	–	200	ppm
		CDR 2nd-order loop enabled	PLL_RXDIVSEL_OUT = 1	–2000	–	2000	ppm
			PLL_RXDIVSEL_OUT = 2	–2000	–	2000	ppm
			PLL_RXDIVSEL_OUT = 4	–1000	–	1000	ppm
SJ Jitter Tolerance(2)							
$JT\_SJ_{3.125}$	Sinusoidal Jitter(3)		3.125 Gb/s	0.4	–	–	UI
$JT\_SJ_{2.5}$	Sinusoidal Jitter(3)		2.5 Gb/s	0.4	–	–	UI
$JT\_SJ_{1.62}$	Sinusoidal Jitter(3)		1.62 Gb/s	0.5	–	–	UI
$JT\_SJ_{1.25}$	Sinusoidal Jitter(3)		1.25 Gb/s	0.5	–	–	UI
JT_SJ_{614}	Sinusoidal Jitter(3)		614 Mb/s	0.5	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)(5)							
$JT\_TJSE_{3.125}$	Total Jitter with stressed eye(4)		3.125 Gb/s	0.65	–	–	UI
$JT\_SJSE_{3.125}$	Sinusoidal Jitter with stressed eye		3.125 Gb/s	0.1	–	–	UI
$JT\_TJSE_{2.7}$	Total Jitter with stressed eye(4)		2.7 Gb/s	0.65	–	–	UI
$JT\_SJSE_{2.7}$	Sinusoidal Jitter with stressed eye		2.7 Gb/s	0.1	–	–	UI

Notes:
1. Using PLL_RXDIVSEL_OUT = 1, 2, and 4.
2. All jitter values are based on a Bit Error Ratio of $1e^{-12}$.
3. Using 80 MHz sinusoidal jitter only in the absence of deterministic and random jitter.
4. Composed of 0.37 UI DJ in the form of ISI and 0.18 UI RJ.
5. Measured using PRBS7 data pattern.

Endpoint Block for PCI Express Designs Switching Characteristics

The Endpoint block for PCI Express is available in the Spartan-6 LXT devices. Consult the Spartan-6 FPGA Integrated Endpoint Block for PCI Express for further information.

Table 24: **Maximum Performance for PCI Express Designs**

Symbol	Description	Speed Grade				Units
		-3	-3N	-2	-1L	
$F_{PCIEUSER}$	User clock maximum frequency	62.5	62.5	62.5	N/A	MHz

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Spartan-6 devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the Switching Characteristics, page 19.

Table 25: **Interface Performances**

Description	I/O Resource	Clock Buffer	Data Width	Speed Grade				Units
				-3	-3N	-2	-1L	
Networking Applications(1)								
SDR LVDS transmitter or receiver	IOB SDR register	BUFG	–	400	400	375	250	Mb/s
DDR LVDS transmitter or receiver	ODDR2/IDDR2 register	2 BUFGs	–	800	800	750	500	Mb/s
SDR LVDS transmitter	OSERDES2	BUFPLL	2	500	500	500	250	Mb/s
			3	750	750	750	375	Mb/s
			4-8	1080	1050	950	500	Mb/s
DDR LVDS transmitter	OSERDES2	2 BUFIO2s	2	500	500	500	250	Mb/s
			3	750	750	750	375	Mb/s
			4-8	1080	1050	950	500	Mb/s
SDR LVDS receiver	ISERDES2 in RETIMED mode	BUFPLL	2	500	500	500	—	Mb/s
			3	750	750	750	—	Mb/s
			4-8	1080	1050	950	—	Mb/s
DDR LVDS receiver	ISERDES2 in RETIMED mode	2 BUFIO2s	2	500	500	500	—	Mb/s
			3	750	750	750	—	Mb/s
			4-8	1080	1050	950	—	Mb/s
Memory Interfaces (Implemented using the Spartan-6 FPGA Memory Controller Block)(2)								
Standard Performance (Standard V_{CCINT})								
DDR				400	Note 4	400	350	Mb/s
DDR2				667	Note 4	625	400	Mb/s
DDR3				800	Note 4	667	—	Mb/s
LPDDR (Mobile_DDR)				400	Note 4	400	350	Mb/s
Extended Performance (Requires Extended Performance V_{CCINT})(3)								
DDR2				800	Note 4	667	—	Mb/s

Notes:

1. Refer to XAPP1064, *Source-Synchronous Serialization and Deserialization (up to 1050 Mb/s)* and UG381, *Spartan-6 FPGA SelectIO Resources User Guide.*
2. Refer to UG388, *Spartan-6 FPGA Memory Controller User Guide*.
3. Extended Memory Controller block performance for DDR2 can be achieved using the extended performance V_{CCINT} range from Table 2.
4. The LX4 device, all devices in the TQG144 and CPG196 packages, and the -3N speed grade do not support a Memory Controller Block.

Switching Characteristics

All values represented in this data sheet are based on these speed specifications: v1.20 for -3, -3N, and -2; and v1.08 for -1L. Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Production

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to Production before faster speed grades.

All specifications are always representative of worst-case supply voltage and junction temperature conditions.

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device.

The -1L speed grade refers to the lower-power Spartan-6 devices. The -3N speed grade refers to the Spartan-6 devices that do not support MCB functionality.

Table 26 correlates the current status of each Spartan-6 device on a per speed grade basis.

Table 26: **Spartan-6 Device Speed Grade Designations**

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC6SLX4[1]			-3, -2, -1L
XC6SLX9			-3, -3N, -2, -1L
XC6SLX16			-3, -3N, -2, -1L
XC6SLX25			-3, -3N, -2, -1L
XC6SLX25T			-3, -3N, -2
XC6SLX45			-3, -3N, -2, -1L
XC6SLX45T			-3, -3N, -2
XC6SLX75			-3, -3N, -2, -1L
XC6SLX75T			-3, -3N, -2
XC6SLX100			-3, -3N, -2, -1L
XC6SLX100T			-3, -3N, -2
XC6SLX150			-3, -3N, -2, -1L
XC6SLX150T			-3, -3N, -2
XA6SLX4			-3, -2
XA6SLX9			-3, -2
XA6SLX16			-3, -2
XA6SLX25			-3, -2
XA6SLX25T			-3, -2
XA6SLX45			-3, -2
XA6SLX45T			-3, -2
XA6SLX75			-3, -2
XA6SLX75T			-3, -2
XA6SLX100			-2
XQ6SLX75			-2, -1L
XQ6SLX75T			-3, -2
XQ6SLX150			-2, -1L
XQ6SLX150T			-3, -2

Notes:

1. The XC6SLX4 is not available in the -3N speed grade.

Testing of Switching Characteristics

All devices are 100% functionally tested. Internal timing parameters are derived from measuring internal test patterns. Listed below are representative values.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Spartan-6 devices.

Production Silicon and ISE Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases. Table 27 lists the production released Spartan-6 family member, speed grade, and the minimum corresponding supported speed specification version and ISE® software revisions. The ISE software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 27: **Spartan-6 Device Production Software and Speed Specification Release(1)**

Device	Speed Grade Designations(2)			
	-3(3)	-3N	-2(4)	-1L
XC6SLX4	ISE 12.4 v1.15	N/A	ISE 12.3 v1.12(5)	ISE 13.2 v1.07
XC6SLX9	ISE 12.4 v1.15	ISE 13.1 Update v1.18(7)	ISE 12.3 v1.12(5)	ISE 13.2 v1.07
XC6SLX16	ISE 12.1 v1.08	ISE 13.1 Update v1.18(7)	ISE 11.5 v1.06	ISE 13.2 v1.07
XC6SLX25	ISE 12.2 v1.11(6)	ISE 13.1 Update v1.18(7)	ISE 12.2 v1.11(6)	ISE 13.2 v1.07
XC6SLX25T	ISE 12.2 v1.11(6)	ISE 13.1 Update v1.18(7)	ISE 12.2 v1.11(6)	N/A
XC6SLX45	ISE 12.1 v1.08	ISE 13.1 Update v1.18(7)	ISE 11.5 v1.07	ISE 13.1 v1.06
XC6SLX45T	ISE 12.1 v1.08	ISE 13.1 Update v1.18(7)	ISE 12.1 v1.08	N/A
XC6SLX75	ISE 12.2 v1.11(6)	ISE 13.1 Update v1.18(7)	ISE 12.2 v1.11(6)	ISE 13.2 v1.07
XC6SLX75T	ISE 12.2 v1.11(6)	ISE 13.1 Update v1.18(7)	ISE 12.2 v1.11(6)	N/A
XC6SLX100	ISE 12.2 v1.11(6)	ISE 13.1 Update v1.18(7)	ISE 12.2 v1.11(6)	ISE 13.1 v1.06
XC6SLX100T	ISE 12.2 v1.11(6)	ISE 13.1 Update v1.18(7)	ISE 12.2 v1.11(6)	N/A
XC6SLX150	ISE 12.2 v1.11(6)	ISE 13.1 Update v1.18(7)	ISE 12.2 v1.11(6)	ISE 13.1 v1.06
XC6SLX150T	ISE 12.2 v1.11(6)	ISE 13.1 Update v1.18(7)	ISE 12.2 v1.11(6)	N/A
XA6SLX4	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX9	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX16	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX25	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX25T	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX45	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX45T	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX75	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX75T	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XA6SLX100	N/A	N/A	ISE 13.3 v1.20	N/A

Table 27: **Spartan-6 Device Production Software and Speed Specification Release[1] *(Cont'd)***

Device	Speed Grade Designations[2]			
	-3[3]	-3N	-2[4]	-1L
XQ6SLX75	N/A	N/A	ISE 13.2 v1.19	ISE 13.2 v1.07
XQ6SLX75T	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A
XQ6SLX150	N/A	N/A	ISE 13.2 v1.19	ISE 13.2 v1.07
XQ6SLX150T	ISE 13.2 v1.19	N/A	ISE 13.2 v1.19	N/A

Notes:
1. ISE 13.3 software with v1.20 for -3, -3N, and -2; and v1.08 for -1L speed specification reflects the changes outlined in XCN11028: *Spartan-6 FPGA Speed File Changes*.
2. As marked with an N/A, LXT devices and all XA devices are not available with a -1L speed grade; LX4 devices and all XA and XQ devices are not available with a -3N speed grade.
3. Improved -3 specifications reflected in this data sheet require ISE 12.4 software with v1.15 speed specification.
4. Improved -2 specifications reflected in this data sheet require ISE 12.4 software and the *12.4 Speed Files Patch* which contains the v1.17 speed specification available on the Xilinx Download Center.
5. ISE 12.3 software with v1.12 speed specification is available using ISE 12.3 software and the *12.3 Speed Files Patch* available on the Xilinx Download Center.
6. ISE 12.2 software with v1.11 speed specification is available using ISE 12.2 software and the *12.2 Speed Files Patch* available on the Xilinx Download Center.
7. ISE 13.1 software with v1.18 speed specification is available using ISE 13.1 software and the *13.1 Update* available on the Xilinx Download Center. See XCN11012: *Speed File Change for -3N Devices*.

IOB Pad Input/Output/3-State Switching Characteristics

Table 28 (for commercial (XC) Spartan-6 devices) and Table 29 (for Automotive XA Spartan-6 and Defense-grade Spartan-6Q devices) summarizes the values of standard-specific data input delays, output delays terminating at pads (based on standard), and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer.

See the TRACE report for further information on delays when using an I/O standard with UNTUNED termination on inputs or outputs.

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices**

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L[1]	-3	-3N	-2	-1L[1]	-3	-3N	-2	-1L[1]	
LVDS_33	1.17	1.29	1.42	1.68	1.55	1.69	1.89	2.42	3000	3000	3000	3000	ns
LVDS_25	1.01	1.13	1.26	1.57	1.65	1.79	1.99	2.47	3000	3000	3000	3000	ns
BLVDS_25	1.02	1.14	1.27	1.57	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
MINI_LVDS_33	1.17	1.29	1.42	1.68	1.57	1.71	1.91	2.41	3000	3000	3000	3000	ns
MINI_LVDS_25	1.01	1.13	1.26	1.57	1.65	1.79	1.99	2.47	3000	3000	3000	3000	ns
LVPECL_33	1.18	1.30	1.43	1.68	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVPECL_25	1.02	1.14	1.27	1.57	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
RSDS_33 (point to point)	1.17	1.29	1.42	1.68	1.57	1.71	1.91	2.42	3000	3000	3000	3000	ns
RSDS_25 (point to point)	1.01	1.13	1.26	1.56	1.65	1.79	1.99	2.47	3000	3000	3000	3000	ns
TMDS_33	1.21	1.33	1.46	1.71	1.54	1.68	1.88	2.50	3000	3000	3000	3000	ns

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L[1]	-3	-3N	-2	-1L[1]	-3	-3N	-2	-1L[1]	
PPDS_33	1.17	1.29	1.42	1.68	1.57	1.71	1.91	2.43	3000	3000	3000	3000	ns
PPDS_25	1.01	1.13	1.26	1.56	1.68	1.82	2.02	2.47	3000	3000	3000	3000	ns
PCI33_3	1.07	1.19	1.32	1.57[2]	3.51	3.65	3.85	4.38[2]	3.51	3.65	3.85	4.38[1]	ns
PCI66_3	1.07	1.19	1.32	1.57[2]	3.53	3.67	3.87	4.39[2]	3.53	3.67	3.87	4.39[1]	ns
DISPLAY_PORT	1.02	1.14	1.27	1.56	3.15	3.29	3.49	4.08	3.15	3.29	3.49	4.08	ns
I2C	1.33	1.45	1.58	1.82	11.56	11.70	11.90	12.52	11.56	11.70	11.90	12.52	ns
SMBUS	1.33	1.45	1.58	1.82	11.56	11.70	11.90	12.52	11.56	11.70	11.90	12.52	ns
SDIO	1.36	1.48	1.61	1.84	2.64	2.78	2.98	3.60	2.64	2.78	2.98	3.60	ns
MOBILE_DDR	0.94	1.06	1.19	1.43	2.35	2.49	2.69	3.31	2.35	2.49	2.69	3.31	ns
HSTL_I	0.90	1.02	1.15	1.39	1.66	1.80	2.00	2.62	1.66	1.80	2.00	2.62	ns
HSTL_II	0.91	1.03	1.16	1.40	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
HSTL_III	0.95	1.07	1.20	1.44	1.67	1.81	2.01	2.61	1.67	1.81	2.01	2.61	ns
HSTL_I _18	0.94	1.06	1.19	1.43	1.77	1.91	2.11	2.73	1.77	1.91	2.11	2.73	ns
HSTL_II _18	0.94	1.06	1.19	1.43	1.85	1.99	2.19	2.81	1.85	1.99	2.19	2.81	ns
HSTL_III _18	0.99	1.11	1.24	1.47	1.79	1.93	2.13	2.72	1.79	1.93	2.13	2.72	ns
SSTL3_I	1.58	1.70	1.83	2.16	1.83	1.97	2.17	2.72	1.83	1.97	2.17	2.72	ns
SSTL3_II	1.58	1.70	1.83	2.16	2.01	2.15	2.35	2.94	2.01	2.15	2.35	2.94	ns
SSTL2_I	1.30	1.42	1.55	1.87	1.77	1.91	2.11	2.69	1.77	1.91	2.11	2.69	ns
SSTL2_II	1.30	1.42	1.55	1.88	1.86	2.00	2.20	2.82	1.86	2.00	2.20	2.82	ns
SSTL18_I	0.92	1.04	1.17	1.41	1.63	1.77	1.97	2.59	1.63	1.77	1.97	2.59	ns
SSTL18_II	0.92	1.04	1.17	1.41	1.66	1.80	2.00	2.62	1.66	1.80	2.00	2.62	ns
SSTL15_II	0.92	1.04	1.17	1.41	1.67	1.81	2.01	2.63	1.67	1.81	2.01	2.63	ns
DIFF_HSTL_I	0.94	1.06	1.19	1.46	1.77	1.91	2.11	2.62	1.77	1.91	2.11	2.62	ns
DIFF_HSTL_II	0.93	1.05	1.18	1.45	1.72	1.86	2.06	2.54	1.72	1.86	2.06	2.54	ns
DIFF_HSTL_III	0.93	1.05	1.18	1.46	1.69	1.83	2.03	2.53	1.69	1.83	2.03	2.53	ns
DIFF_HSTL_I_18	0.97	1.09	1.22	1.50	1.79	1.93	2.13	2.63	1.79	1.93	2.13	2.63	ns
DIFF_HSTL_II_18	0.97	1.09	1.22	1.49	1.69	1.83	2.03	2.51	1.69	1.83	2.03	2.51	ns
DIFF_HSTL_III_18	0.97	1.09	1.22	1.50	1.69	1.83	2.03	2.53	1.69	1.83	2.03	2.53	ns
DIFF_SSTL3_I	1.18	1.30	1.43	1.68	1.81	1.95	2.15	2.64	1.81	1.95	2.15	2.64	ns
DIFF_SSTL3_II	1.19	1.31	1.44	1.68	1.80	1.94	2.14	2.63	1.80	1.94	2.14	2.63	ns
DIFF_SSTL2_I	1.02	1.14	1.27	1.57	1.80	1.94	2.14	2.62	1.80	1.94	2.14	2.62	ns
DIFF_SSTL2_II	1.02	1.14	1.27	1.57	1.76	1.90	2.10	2.57	1.76	1.90	2.10	2.57	ns
DIFF_SSTL18_I	0.97	1.09	1.22	1.51	1.72	1.86	2.06	2.56	1.72	1.86	2.06	2.56	ns
DIFF_SSTL18_II	0.98	1.10	1.23	1.50	1.68	1.82	2.02	2.52	1.68	1.82	2.02	2.52	ns
DIFF_SSTL15_II	0.94	1.06	1.19	1.46	1.67	1.81	2.01	2.50	1.67	1.81	2.01	2.50	ns
DIFF_MOBILE_DDR	0.97	1.09	1.22	1.51	1.75	1.89	2.09	2.57	1.75	1.89	2.09	2.57	ns

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L[1]	-3	-3N	-2	-1L[1]	-3	-3N	-2	-1L[1]	
LVTTL, QUIETIO, 2 mA	1.35	1.47	1.60	1.82	5.39	5.53	5.73	6.37	5.39	5.53	5.73	6.37	ns
LVTTL, QUIETIO, 4 mA	1.35	1.47	1.60	1.82	4.29	4.43	4.63	5.22	4.29	4.43	4.63	5.22	ns
LVTTL, QUIETIO, 6 mA	1.35	1.47	1.60	1.82	3.75	3.89	4.09	4.69	3.75	3.89	4.09	4.69	ns
LVTTL, QUIETIO, 8 mA	1.35	1.47	1.60	1.82	3.23	3.37	3.57	4.20	3.23	3.37	3.57	4.20	ns
LVTTL, QUIETIO, 12 mA	1.35	1.47	1.60	1.82	3.28	3.42	3.62	4.22	3.28	3.42	3.62	4.22	ns
LVTTL, QUIETIO, 16 mA	1.35	1.47	1.60	1.82	2.94	3.08	3.28	3.92	2.94	3.08	3.28	3.92	ns
LVTTL, QUIETIO, 24 mA	1.35	1.47	1.60	1.82	2.69	2.83	3.03	3.67	2.69	2.83	3.03	3.67	ns
LVTTL, Slow, 2 mA	1.35	1.47	1.60	1.82	4.36	4.50	4.70	5.30	4.36	4.50	4.70	5.30	ns
LVTTL, Slow, 4 mA	1.35	1.47	1.60	1.82	3.17	3.31	3.51	4.16	3.17	3.31	3.51	4.16	ns
LVTTL, Slow, 6 mA	1.35	1.47	1.60	1.82	2.76	2.90	3.10	3.75	2.76	2.90	3.10	3.75	ns
LVTTL, Slow, 8 mA	1.35	1.47	1.60	1.82	2.59	2.73	2.93	3.55	2.59	2.73	2.93	3.55	ns
LVTTL, Slow, 12 mA	1.35	1.47	1.60	1.82	2.58	2.72	2.92	3.54	2.58	2.72	2.92	3.54	ns
LVTTL, Slow, 16 mA	1.35	1.47	1.60	1.82	2.39	2.53	2.73	3.40	2.39	2.53	2.73	3.40	ns
LVTTL, Slow, 24 mA	1.35	1.47	1.60	1.82	2.28	2.42	2.62	3.24	2.28	2.42	2.62	3.24	ns
LVTTL, Fast, 2 mA	1.35	1.47	1.60	1.82	3.78	3.92	4.12	4.74	3.78	3.92	4.12	4.74	ns
LVTTL, Fast, 4 mA	1.35	1.47	1.60	1.82	2.49	2.63	2.83	3.45	2.49	2.63	2.83	3.45	ns
LVTTL, Fast, 6 mA	1.35	1.47	1.60	1.82	2.44	2.58	2.78	3.40	2.44	2.58	2.78	3.40	ns
LVTTL, Fast, 8 mA	1.35	1.47	1.60	1.82	2.32	2.46	2.66	3.28	2.32	2.46	2.66	3.28	ns
LVTTL, Fast, 12 mA	1.35	1.47	1.60	1.82	1.83	1.97	2.17	2.79	1.83	1.97	2.17	2.79	ns
LVTTL, Fast, 16 mA	1.35	1.47	1.60	1.82	1.83	1.97	2.17	2.79	1.83	1.97	2.17	2.79	ns
LVTTL, Fast, 24 mA	1.35	1.47	1.60	1.82	1.83	1.97	2.17	2.79	1.83	1.97	2.17	2.79	ns
LVCMOS33, QUIETIO, 2 mA	1.34	1.46	1.59	1.82	5.40	5.54	5.74	6.37	5.40	5.54	5.74	6.37	ns
LVCMOS33, QUIETIO, 4 mA	1.34	1.46	1.59	1.82	4.03	4.17	4.37	5.01	4.03	4.17	4.37	5.01	ns
LVCMOS33, QUIETIO, 6 mA	1.34	1.46	1.59	1.82	3.51	3.65	3.85	4.47	3.51	3.65	3.85	4.47	ns
LVCMOS33, QUIETIO, 8 mA	1.34	1.46	1.59	1.82	3.37	3.51	3.71	4.33	3.37	3.51	3.71	4.33	ns
LVCMOS33, QUIETIO, 12 mA	1.34	1.46	1.59	1.82	2.94	3.08	3.28	3.93	2.94	3.08	3.28	3.93	ns
LVCMOS33, QUIETIO, 16 mA	1.34	1.46	1.59	1.82	2.77	2.91	3.11	3.78	2.77	2.91	3.11	3.78	ns
LVCMOS33, QUIETIO, 24 mA	1.34	1.46	1.59	1.82	2.59	2.73	2.93	3.58	2.59	2.73	2.93	3.58	ns
LVCMOS33, Slow, 2 mA	1.34	1.46	1.59	1.82	4.37	4.51	4.71	5.28	4.37	4.51	4.71	5.28	ns
LVCMOS33, Slow, 4 mA	1.34	1.46	1.59	1.82	2.98	3.12	3.32	3.94	2.98	3.12	3.32	3.94	ns
LVCMOS33, Slow, 6 mA	1.34	1.46	1.59	1.82	2.58	2.72	2.92	3.61	2.58	2.72	2.92	3.61	ns
LVCMOS33, Slow, 8 mA	1.34	1.46	1.59	1.82	2.65	2.79	2.99	3.61	2.65	2.79	2.99	3.61	ns
LVCMOS33, Slow, 12 mA	1.34	1.46	1.59	1.82	2.39	2.53	2.73	3.31	2.39	2.53	2.73	3.31	ns
LVCMOS33, Slow, 16 mA	1.34	1.46	1.59	1.82	2.31	2.45	2.65	3.27	2.31	2.45	2.65	3.27	ns
LVCMOS33, Slow, 24 mA	1.34	1.46	1.59	1.82	2.28	2.42	2.62	3.24	2.28	2.42	2.62	3.24	ns
LVCMOS33, Fast, 2 mA	1.34	1.46	1.59	1.82	3.76	3.90	4.10	4.70	3.76	3.90	4.10	4.70	ns
LVCMOS33, Fast, 4 mA	1.34	1.46	1.59	1.82	2.48	2.62	2.82	3.44	2.48	2.62	2.82	3.44	ns
LVCMOS33, Fast, 6 mA	1.34	1.46	1.59	1.82	2.32	2.46	2.66	3.28	2.32	2.46	2.66	3.28	ns

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L[1]	-3	-3N	-2	-1L[1]	-3	-3N	-2	-1L[1]	
LVCMOS33, Fast, 8 mA	1.34	1.46	1.59	1.82	2.07	2.21	2.41	3.03	2.07	2.21	2.41	3.03	ns
LVCMOS33, Fast, 12 mA	1.34	1.46	1.59	1.82	1.65	1.79	1.99	2.62	1.65	1.79	1.99	2.62	ns
LVCMOS33, Fast, 16 mA	1.34	1.46	1.59	1.82	1.65	1.79	1.99	2.62	1.65	1.79	1.99	2.62	ns
LVCMOS33, Fast, 24 mA	1.34	1.46	1.59	1.82	1.65	1.79	1.99	2.62	1.65	1.79	1.99	2.62	ns
LVCMOS25, QUIETIO, 2 mA	0.82	0.94	1.07	1.31	4.81	4.95	5.15	5.79	4.81	4.95	5.15	5.79	ns
LVCMOS25, QUIETIO, 4 mA	0.82	0.94	1.07	1.31	3.70	3.84	4.04	4.66	3.70	3.84	4.04	4.66	ns
LVCMOS25, QUIETIO, 6 mA	0.82	0.94	1.07	1.31	3.46	3.60	3.80	4.38	3.46	3.60	3.80	4.38	ns
LVCMOS25, QUIETIO, 8 mA	0.82	0.94	1.07	1.31	3.20	3.34	3.54	4.12	3.20	3.34	3.54	4.12	ns
LVCMOS25, QUIETIO, 12 mA	0.82	0.94	1.07	1.31	2.83	2.97	3.17	3.75	2.83	2.97	3.17	3.75	ns
LVCMOS25, QUIETIO, 16 mA	0.82	0.94	1.07	1.31	2.64	2.78	2.98	3.64	2.64	2.78	2.98	3.64	ns
LVCMOS25, QUIETIO, 24 mA	0.82	0.94	1.07	1.31	2.45	2.59	2.79	3.42	2.45	2.59	2.79	3.42	ns
LVCMOS25, Slow, 2 mA	0.82	0.94	1.07	1.31	3.78	3.92	4.12	4.76	3.78	3.92	4.12	4.76	ns
LVCMOS25, Slow, 4 mA	0.82	0.94	1.07	1.31	2.79	2.93	3.13	3.73	2.79	2.93	3.13	3.73	ns
LVCMOS25, Slow, 6 mA	0.82	0.94	1.07	1.31	2.73	2.87	3.07	3.66	2.73	2.87	3.07	3.66	ns
LVCMOS25, Slow, 8 mA	0.82	0.94	1.07	1.31	2.48	2.62	2.82	3.42	2.48	2.62	2.82	3.42	ns
LVCMOS25, Slow, 12 mA	0.82	0.94	1.07	1.31	2.01	2.15	2.35	2.95	2.01	2.15	2.35	2.95	ns
LVCMOS25, Slow, 16 mA	0.82	0.94	1.07	1.31	2.01	2.15	2.35	2.95	2.01	2.15	2.35	2.95	ns
LVCMOS25, Slow, 24 mA	0.82	0.94	1.07	1.31	2.01	2.15	2.35	2.94	2.01	2.15	2.35	2.94	ns
LVCMOS25, Fast, 2 mA	0.82	0.94	1.07	1.31	3.35	3.49	3.69	4.31	3.35	3.49	3.69	4.31	ns
LVCMOS25, Fast, 4 mA	0.82	0.94	1.07	1.31	2.25	2.39	2.59	3.22	2.25	2.39	2.59	3.22	ns
LVCMOS25, Fast, 6 mA	0.82	0.94	1.07	1.31	2.09	2.23	2.43	3.05	2.09	2.23	2.43	3.05	ns
LVCMOS25, Fast, 8 mA	0.82	0.94	1.07	1.31	2.02	2.16	2.36	2.98	2.02	2.16	2.36	2.98	ns
LVCMOS25, Fast, 12 mA	0.82	0.94	1.07	1.31	1.56	1.70	1.90	2.52	1.56	1.70	1.90	2.52	ns
LVCMOS25, Fast, 16 mA	0.82	0.94	1.07	1.31	1.56	1.70	1.90	2.52	1.56	1.70	1.90	2.52	ns
LVCMOS25, Fast, 24 mA	0.82	0.94	1.07	1.31	1.56	1.70	1.90	2.52	1.56	1.70	1.90	2.52	ns
LVCMOS18, QUIETIO, 2 mA	1.18	1.30	1.43	2.04	5.92	6.06	6.26	6.80	5.92	6.06	6.26	6.80	ns
LVCMOS18, QUIETIO, 4 mA	1.18	1.30	1.43	2.04	4.74	4.88	5.08	5.63	4.74	4.88	5.08	5.63	ns
LVCMOS18, QUIETIO, 6 mA	1.18	1.30	1.43	2.04	4.05	4.19	4.39	4.96	4.05	4.19	4.39	4.96	ns
LVCMOS18, QUIETIO, 8 mA	1.18	1.30	1.43	2.04	3.71	3.85	4.05	4.63	3.71	3.85	4.05	4.63	ns
LVCMOS18, QUIETIO, 12 mA	1.18	1.30	1.43	2.04	3.35	3.49	3.69	4.27	3.35	3.49	3.69	4.27	ns
LVCMOS18, QUIETIO, 16 mA	1.18	1.30	1.43	2.04	3.20	3.34	3.54	4.14	3.20	3.34	3.54	4.14	ns
LVCMOS18, QUIETIO, 24 mA	1.18	1.30	1.43	2.04	2.96	3.10	3.30	3.98	2.96	3.10	3.30	3.98	ns
LVCMOS18, Slow, 2 mA	1.18	1.30	1.43	2.04	4.62	4.76	4.96	5.54	4.62	4.76	4.96	5.54	ns
LVCMOS18, Slow, 4 mA	1.18	1.30	1.43	2.04	3.69	3.83	4.03	4.60	3.69	3.83	4.03	4.60	ns
LVCMOS18, Slow, 6 mA	1.18	1.30	1.43	2.04	3.00	3.14	3.34	3.94	3.00	3.14	3.34	3.94	ns
LVCMOS18, Slow, 8 mA	1.18	1.30	1.43	2.04	2.19	2.33	2.53	3.17	2.19	2.33	2.53	3.17	ns
LVCMOS18, Slow, 12 mA	1.18	1.30	1.43	2.04	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18, Slow, 16 mA	1.18	1.30	1.43	2.04	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns

Table 28: **IOB Switching Characteristics for the Commercial (XC) Spartan-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-3N	-2	-1L[1]	-3	-3N	-2	-1L[1]	-3	-3N	-2	-1L[1]	
LVCMOS18, Slow, 24 mA	1.18	1.30	1.43	2.04	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18, Fast, 2 mA	1.18	1.30	1.43	2.04	3.59	3.73	3.93	4.53	3.59	3.73	3.93	4.53	ns
LVCMOS18, Fast, 4 mA	1.18	1.30	1.43	2.04	2.39	2.53	2.73	3.35	2.39	2.53	2.73	3.35	ns
LVCMOS18, Fast, 6 mA	1.18	1.30	1.43	2.04	1.88	2.02	2.22	2.84	1.88	2.02	2.22	2.84	ns
LVCMOS18, Fast, 8 mA	1.18	1.30	1.43	2.04	1.81	1.95	2.15	2.77	1.81	1.95	2.15	2.77	ns
LVCMOS18, Fast, 12 mA	1.18	1.30	1.43	2.04	1.71	1.85	2.05	2.67	1.71	1.85	2.05	2.67	ns
LVCMOS18, Fast, 16 mA	1.18	1.30	1.43	2.04	1.71	1.85	2.05	2.67	1.71	1.85	2.05	2.67	ns
LVCMOS18, Fast, 24 mA	1.18	1.30	1.43	2.04	1.71	1.85	2.05	2.67	1.71	1.85	2.05	2.67	ns
LVCMOS18_JEDEC, QUIETIO, 2 mA	0.94	1.06	1.19	1.41	5.91	6.05	6.25	6.79	5.91	6.05	6.25	6.79	ns
LVCMOS18_JEDEC, QUIETIO, 4 mA	0.94	1.06	1.19	1.41	4.75	4.89	5.09	5.64	4.75	4.89	5.09	5.64	ns
LVCMOS18_JEDEC, QUIETIO, 6 mA	0.94	1.06	1.19	1.41	4.04	4.18	4.38	4.96	4.04	4.18	4.38	4.96	ns
LVCMOS18_JEDEC, QUIETIO, 8 mA	0.94	1.06	1.19	1.41	3.71	3.85	4.05	4.62	3.71	3.85	4.05	4.62	ns
LVCMOS18_JEDEC, QUIETIO, 12 mA	0.94	1.06	1.19	1.41	3.35	3.49	3.69	4.28	3.35	3.49	3.69	4.28	ns
LVCMOS18_JEDEC, QUIETIO, 16 mA	0.94	1.06	1.19	1.41	3.20	3.34	3.54	4.13	3.20	3.34	3.54	4.13	ns
LVCMOS18_JEDEC, QUIETIO, 24 mA	0.94	1.06	1.19	1.41	2.96	3.10	3.30	3.98	2.96	3.10	3.30	3.98	ns
LVCMOS18_JEDEC, Slow, 2 mA	0.94	1.06	1.19	1.41	4.59	4.73	4.93	5.54	4.59	4.73	4.93	5.54	ns
LVCMOS18_JEDEC, Slow, 4 mA	0.94	1.06	1.19	1.41	3.69	3.83	4.03	4.60	3.69	3.83	4.03	4.60	ns
LVCMOS18_JEDEC, Slow, 6 mA	0.94	1.06	1.19	1.41	3.00	3.14	3.34	3.94	3.00	3.14	3.34	3.94	ns
LVCMOS18_JEDEC, Slow, 8 mA	0.94	1.06	1.19	1.41	2.19	2.33	2.53	3.18	2.19	2.33	2.53	3.18	ns
LVCMOS18_JEDEC, Slow, 12 mA	0.94	1.06	1.19	1.41	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18_JEDEC, Slow, 16 mA	0.94	1.06	1.19	1.41	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18_JEDEC, Slow, 24 mA	0.94	1.06	1.19	1.41	1.99	2.13	2.33	2.95	1.99	2.13	2.33	2.95	ns
LVCMOS18_JEDEC, Fast, 2 mA	0.94	1.06	1.19	1.41	3.57	3.71	3.91	4.52	3.57	3.71	3.91	4.52	ns
LVCMOS18_JEDEC, Fast, 4 mA	0.94	1.06	1.19	1.41	2.39	2.53	2.73	3.35	2.39	2.53	2.73	3.35	ns
LVCMOS18_JEDEC, Fast, 6 mA	0.94	1.06	1.19	1.41	1.88	2.02	2.22	2.84	1.88	2.02	2.22	2.84	ns
LVCMOS18_JEDEC, Fast, 8 mA	0.94	1.06	1.19	1.41	1.80	1.94	2.14	2.76	1.80	1.94	2.14	2.76	ns
LVCMOS18_JEDEC, Fast, 12 mA	0.94	1.06	1.19	1.41	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
LVCMOS18_JEDEC, Fast, 16 mA	0.94	1.06	1.19	1.41	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
LVCMOS18_JEDEC, Fast, 24 mA	0.94	1.06	1.19	1.41	1.72	1.86	2.06	2.68	1.72	1.86	2.06	2.68	ns
LVCMOS15, QUIETIO, 2 mA	0.98	1.10	1.23	1.79	5.47	5.61	5.81	6.38	5.47	5.61	5.81	6.38	ns
LVCMOS15, QUIETIO, 4 mA	0.98	1.10	1.23	1.79	4.61	4.75	4.95	5.51	4.61	4.75	4.95	5.51	ns
LVCMOS15, QUIETIO, 6 mA	0.98	1.10	1.23	1.79	4.07	4.21	4.41	4.97	4.07	4.21	4.41	4.97	ns
LVCMOS15, QUIETIO, 8 mA	0.98	1.10	1.23	1.79	3.91	4.05	4.25	4.81	3.91	4.05	4.25	4.81	ns
LVCMOS15, QUIETIO, 12 mA	0.98	1.10	1.23	1.79	3.53	3.67	3.87	4.51	3.53	3.67	3.87	4.51	ns
LVCMOS15, QUIETIO, 16 mA	0.98	1.10	1.23	1.79	3.32	3.46	3.66	4.31	3.32	3.46	3.66	4.31	ns
LVCMOS15, Slow, 2 mA	0.98	1.10	1.23	1.79	4.18	4.32	4.52	5.11	4.18	4.32	4.52	5.11	ns
LVCMOS15, Slow, 4 mA	0.98	1.10	1.23	1.79	3.42	3.56	3.76	4.34	3.42	3.56	3.76	4.34	ns
LVCMOS15, Slow, 6 mA	0.98	1.10	1.23	1.79	2.29	2.43	2.63	3.24	2.29	2.43	2.63	3.24	ns